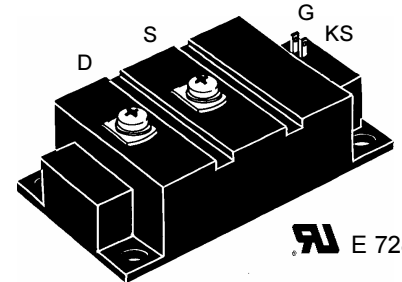
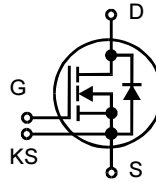



MegaMOS™FET Module

VMO 500-02F

$V_{DSS} = 200 \text{ V}$
 $I_{D25} = 500 \text{ A}$
 $R_{DS(on) \text{ typ}} = 3.5 \text{ m}\Omega$

N-Channel Enhancement Mode



 E 72873

C3

D = Drain
S = Source
KS = Kelvin Source
G = Gate

Symbol	Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	200	V
V_{DGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 10 \text{ k}\Omega$	200	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$ *	500	A
I_{D80}	$T_C = 80^\circ\text{C}$	370	A
I_{DM}	$T_C = 25^\circ\text{C}, t_p = 10 \mu\text{s}$ *	2000	A
P_D	$T_C = 25^\circ\text{C}$	2200	W
T_J		-40 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-40 ... +125	$^\circ\text{C}$
V_{ISOL}	50/60 Hz $I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ min}$ $t = 1 \text{ s}$	3000 V~ 3600 V~
M_d	Mounting torque (M6) Terminal connection torque (M5)	2.25-2.75/20-25 2.5-3.7/22-33	Nm/lb.in. Nm/lb.in.
Weight	typical including screws	250	g

Features

- International standard package
- Direct Copper Bonded Al_2O_3 ceramic base plate
- Low $R_{DS(on)}$ HDMOS™ process
- Low package inductance for high speed switching
- Kelvin Source contact for easy drive

Applications

- AC motor speed control for electric vehicles
- DC servo and robot drives
- Switched-mode and resonant-mode power supplies
- DC choppers

Advantages

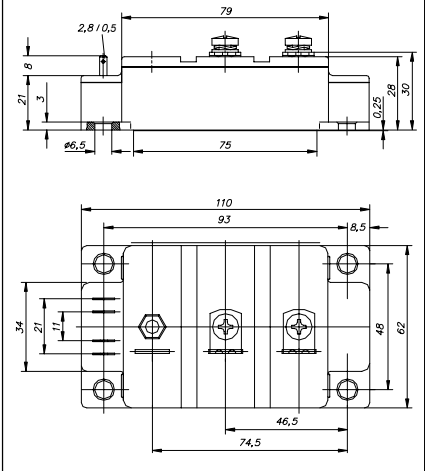
- Easy to mount
- Space and weight savings
- High power density
- Low losses

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}, I_D = 12 \text{ mA}$	200		V
$V_{GS(th)}$	$V_{DS} = 20 \text{ V}, I_D = 44 \text{ mA}$	2		4 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V DC}, V_{DS} = 0$			$\pm 500 \text{ nA}$
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}, V_{GS} = 0 \text{ V}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			2.4 mA 12 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}, I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$		3.5	4.2 $\text{m}\Omega$

* Additional current limitation by external leads

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$ pulsed		420	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		57	nF
C_{oss}			10	nF
C_{rss}			3.7	nF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\ \Omega$		210	ns
t_r			500	ns
$t_{d(off)}$			900	ns
t_f			350	ns
Q_g	$V_{GS} = 10\text{ V}, V_{DS} = 100\text{ V}, I_D = 200\text{ A}$		2500	nC
Q_{gs}			450	nC
Q_{gd}			1200	nC
R_{thJC}	with 30 μm heat transfer paste			0.057 K/W
R_{thJK}			0.085	K/W

Dimensions in mm (1 mm = 0.0394")



C3

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0, T_C = 25^\circ\text{C}, T_J = T_{JM}$ *			500 A
I_{SM}	Repetitive; pulse width limited by T_{JM} *			2000 A
V_{SD}	$I_F = 500\text{ A}; V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$		1	1.25 V
t_{rr}	$I_F = I_S, -di/dt = 1200\text{ A}/\mu\text{s}, V_{DS} = 100\text{ V}$		600	ns

* Additional current limitation by external leads

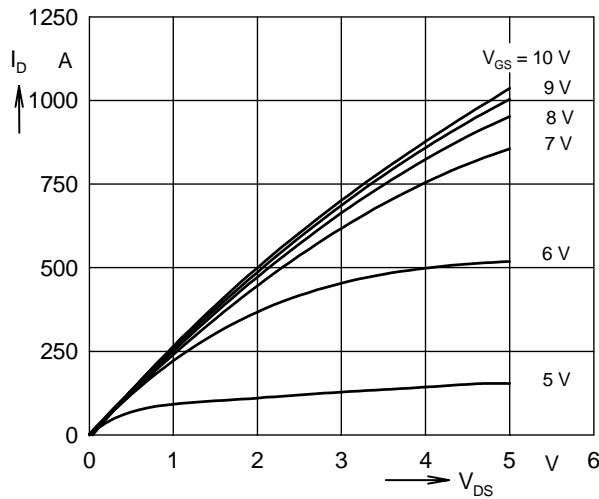


Fig. 1 Typical output characteristics $I_D = f(V_{DS})$

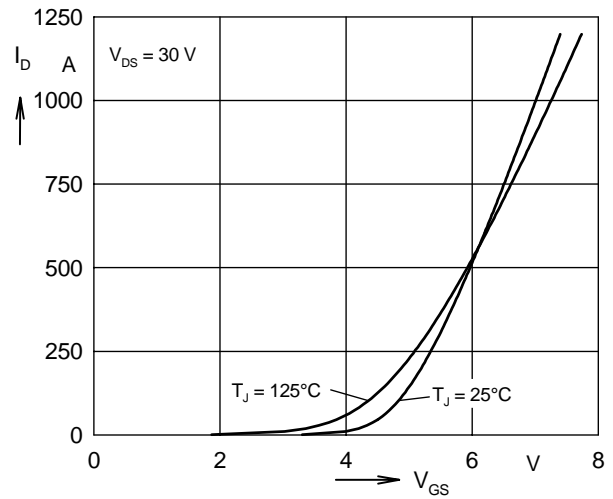


Fig. 2 Typical transfer characteristics $I_D = f(V_{GS})$

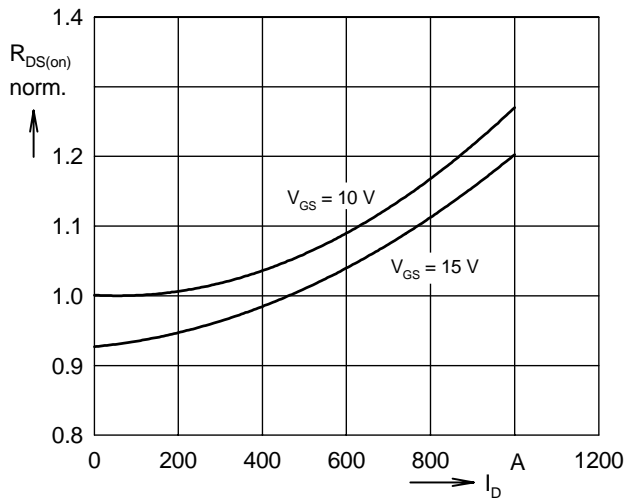


Fig. 3 Typical $R_{DS(on)} = f(I_D)$, normalized

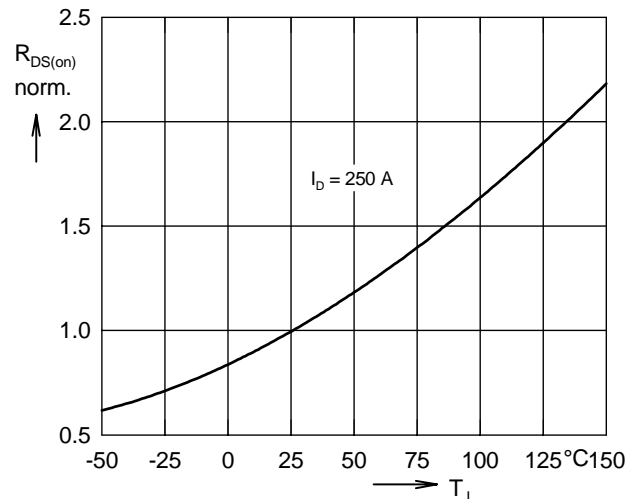


Fig. 4 $R_{DS(on)} = f(T_J)$, normalized

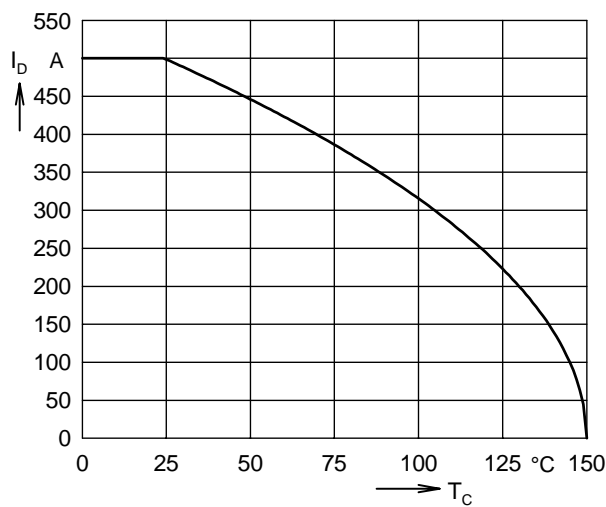


Fig. 5 Continuous drain current $I_D = f(T_C)$

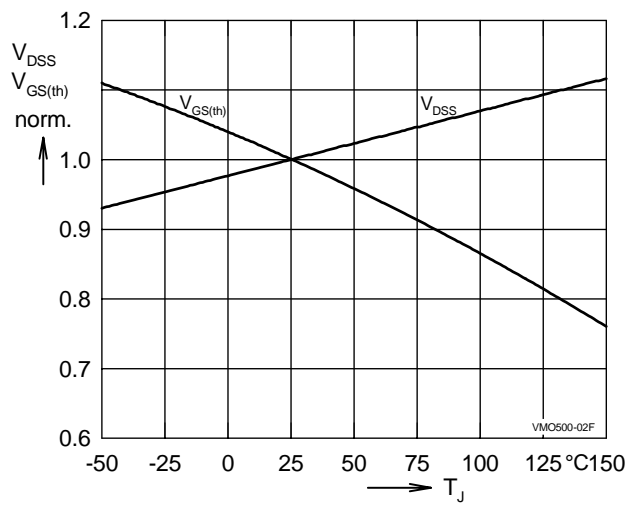


Fig. 6 $V_{DS} = f(T_J)$, $V_{GS(th)} = f(T_J)$, normalized

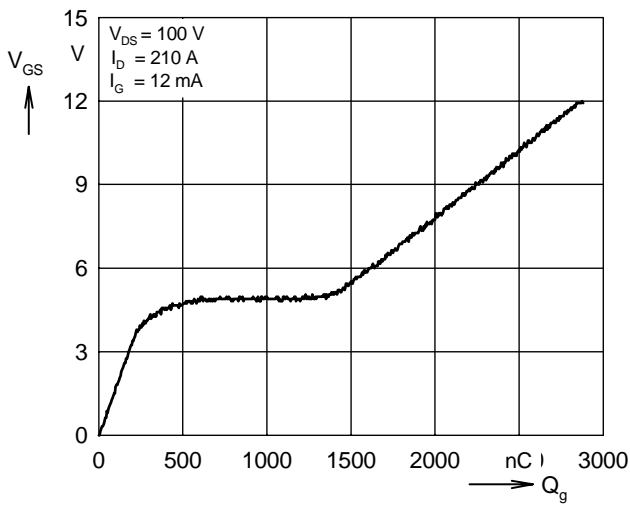


Fig. 7 Typical turn-on gate charge characteristics

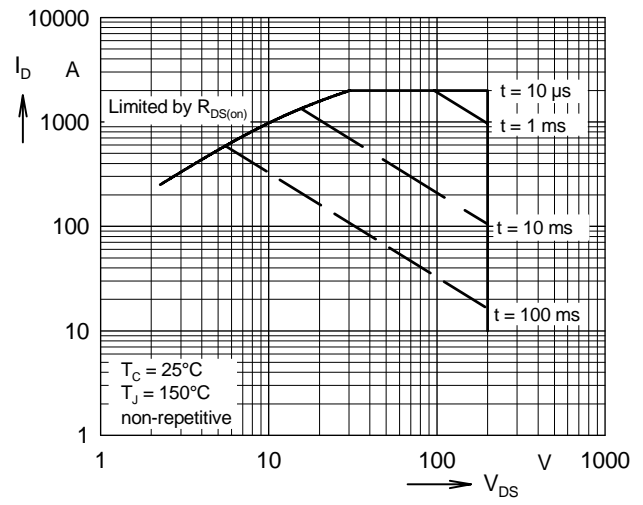


Fig. 8 Forward Bias Safe Operating Area, $I_D = f(V_{DS})$

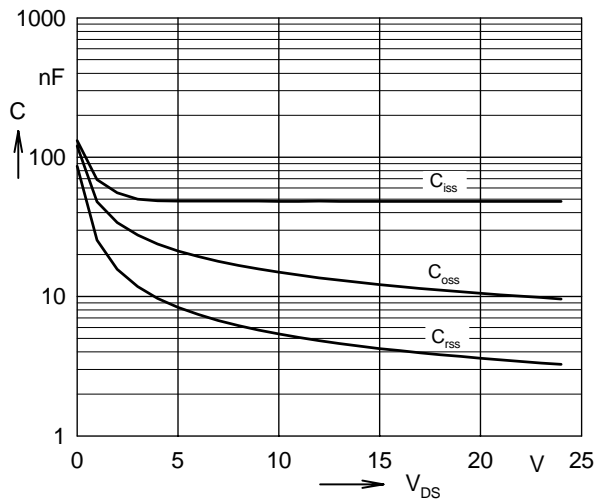


Fig. 9 Typical capacitances $C = f(V_{DS})$, $f = 1 \text{ MHz}$

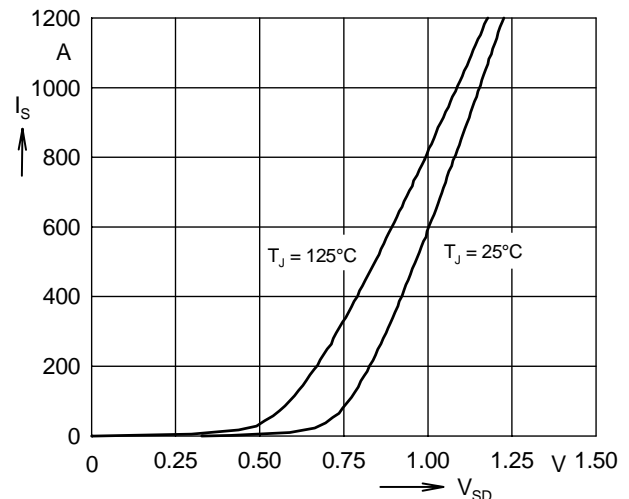


Fig. 10 Typical forward characteristics of reverse diode, $I_S = f(V_{SD})$

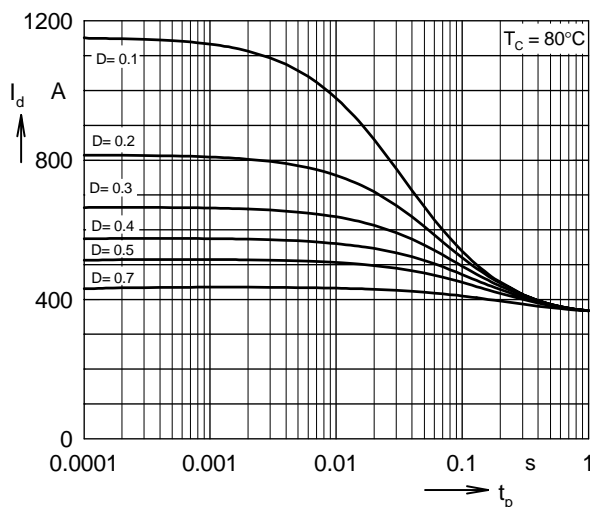


Fig. 11 Drain current versus pulse width and duty cycle

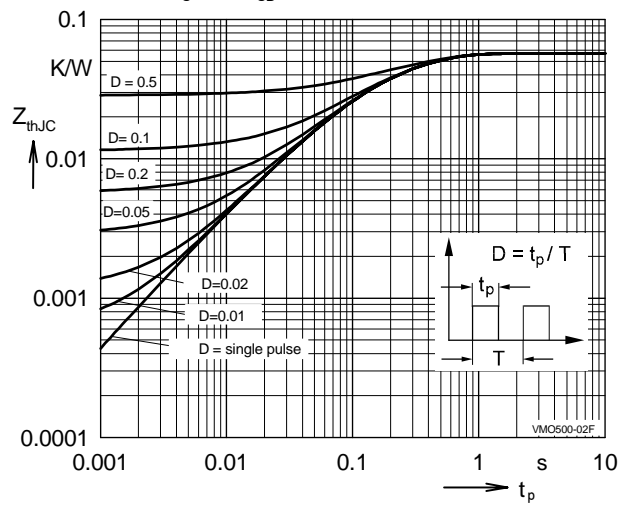


Fig. 12 Transient thermal resistance $Z_{thJC} = f(t_p)$